

1MBI2400VC-170E

IGBT Modules

IGBT MODULE (V series) 1700V / 2400A / 1 in one package

■ Features

High speed switching Voltage drive Low Inductance module structure

Applications

Inverter for Motor Drive AC and DC Servo Drive Amplifier Uninterruptible Power Supply Industrial machines, such as Welding machines



■ Maximum Ratings and Characteristics

■ Absolute Maximum Ratings (at Tc=25°C unless otherwise specified)

Items	Symbols	Conditions		Maximum ratings		
Collector-Emitter voltage	Vces			1700		
Gate-Emitter voltage	V _{GES}			±20	V	
	l _c	Continuous	Tc=25°C	3600		
			Tc=100°C	2400		
Collector current	I _{cp}	1ms		4800	Α	
	-l _c			2400		
	-I _{c pulse}	1ms		4800		
Collector power dissipation	Pc	1 device		15000	W	
Junction temperature	Tj			175		
Operating junction temperature (under switching conditions)	Тјор			150	°C	
Storage temperature	T _{stg}			-40 ~ +150		
Isolation voltage Between terminal and copper base (*1)	Viso	AC : 1min.		4000	VAC	
	Mounting	M6 M8		5.75	Nm	
Screw torque (*2)	Main Terminals			10		
	Sense Terminals	M4		2.5		

Note *1: All terminals should be connected together when isolation test will be done. Note *2: Recommendable Value :

Mounting 4.25~5.75 Nm $\,$ (M6) , Main Terminals 8~10 Nm $\,$ (M8) , Sense Terminals 1.7~2.5 Nm $\,$ (M4)

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● Electrical characteristics (at Tj= 25°C unless otherwise specified)

Home	Cymhala	Conditions		Characteristics			l lucita
Items	Symbols			min.	typ.	max.	Units
Zero gate voltage collector current	Ices	V _{GE} = 0V, V _{CE} = 1700V		-	-	1.0	mA
Gate-Emitter leakage current	Iges	V _{CE} = 0V, V _{GE} =±20V		-	-	3200	nA
Gate-Emitter threshold voltage	V _{GE(th)}	VcE = 20V, Ic = 2400mA		6.0	6.5	7.0	V
_		V _{GE} =15V I _c = 2400A	T _j =25°C	-	2.32	2.61	V
	V _{CE(sat)} (main terminal)		T _j =125°C	-	2.72	-	
Callagton Emitten activistics valtage	(main terminal)		T _j =150°C	-	2.77	-	
Collector-Emitter saturation voltage	.,		T _j =25°C	-	2.00	2.25	
	V _{CE(sat)} (chip)		T _j =125°C	-	2.40	-	
	(Criip)		T _j =150°C	-	2.45	-	
Internal gate resistance	Int Rg			-	0.94	-	Ω
Input capacitance	Cies	V _{CE} =10V, V _{GE} =0V, f=1MHz		-	218	-	nF
Turn-on	ton	Vcc = 900V, Ic = 2400A		-	2.63	-	μs
	tr	Lm = 56nH, V _{GE} =±15V,	-	0.94	-		
Turn-off	toff	Rgon = 0.82Ω Rgoff = 0.39Ω		-	2.41	-	
	tr			-	0.38	-	
	.,	V _{GE} =0V I _F = 2400A	T _j =25°C	-	2.12	2.52	- V
Forward on voltage	V₅ (main terminal)		T _j =125°C	-	2.32	-	
	(main terminar)		T _j =150°C	-	2.30	-	
			T _j =25°C	-	1.80	2.15	
	V _F (chip)		T _j =125°C	-	2.00	-	
	(CIIIP)		T _j =150°C	-	1.98	-	
Reverse recovery	trr	I _F = 2400A,T _j =125°C		-	0.60		μs
Lead resistance, terminal-chip	R lead			-	0.134		mΩ

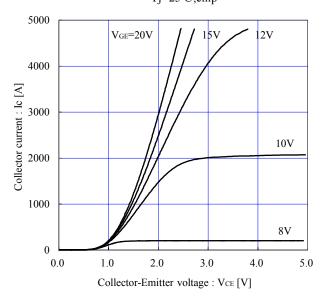
● Thermal resistance characteristics

Items	Symbols	Conditions	Characteristics			Units	
items Symbo		Conditions	min.	typ.	max.	Ullits	
Thermal resistance	R _{th(j-c)}	IGBT	-	-	0.0100		
		FWD	-	-	0.0165	°C/W	
Contact thermal resistance (*3)	R _{th(c-f)}	with Thermal Compound	-	0.006	-		

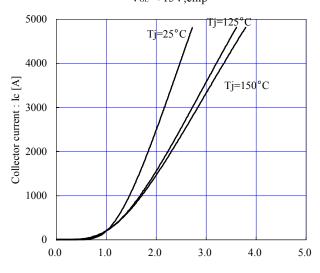
Note $^{\star}3$: This is the value which is defined mounting on the additional cooling fin with thermal compound.

■ Characteristics (Representative)

Collector current vs. Collector-Emitter voltage (typ.) $Tj{=}25^{\circ}C, chip$

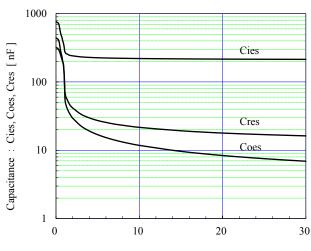


Collector current vs. Collector-Emitter voltage (typ.) V_{GE} =+15V,chip



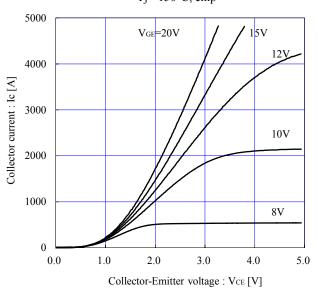
Collector-Emitter voltage: VCE [V]

Capacitance vs. Collector-Emitter voltage (typ.) V_{GE}=0V, f= 1MHz, Tj= 25°C



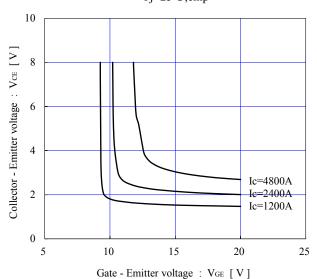
Collector-Emitter voltage : VCE [V]

Collector current vs. Collector-Emitter voltage (typ.) Tj= 150°C, chip

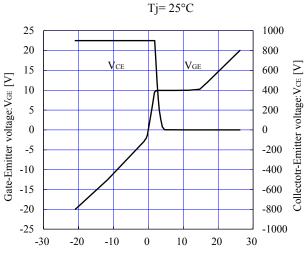


Collector-Emitter voltage vs. Gate-Emitter voltage (typ.)

Tj=25°C,chip

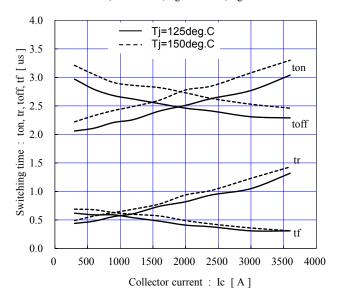


Dynamic Gate charge (typ.)

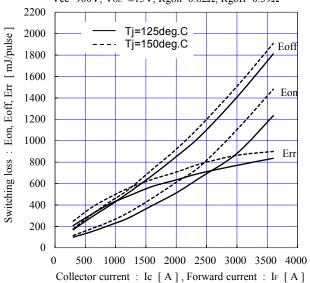


Gate charge : Qg [uC]

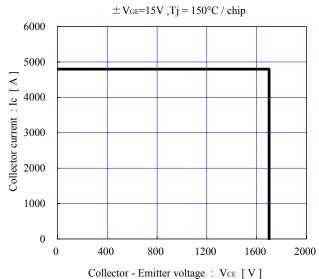
Switching time vs. Collector current (typ.) Vcc=900V, V_{GE} =±15V, Rgon=0.82 Ω , Rgoff=0.39 Ω



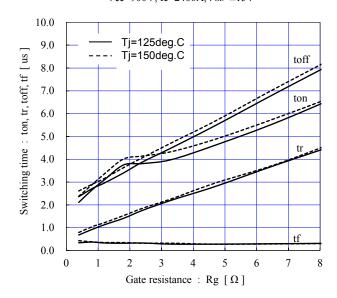
Switching loss vs. Collector current (typ.) Vcc=900V, V_{GE}= ± 15 V, Rgon= 0.82Ω , Rgoff= 0.39Ω



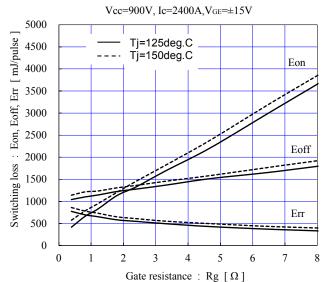
Reverse bias safe operating area (max.)

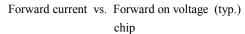


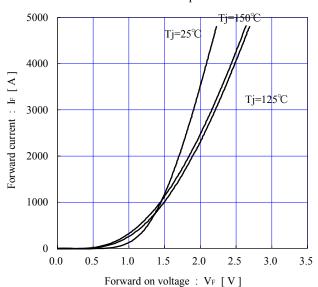
Switching time vs. Gate resistance (typ.) Vcc=900V, Ic=2400A, $V_{GE}=\pm15V$



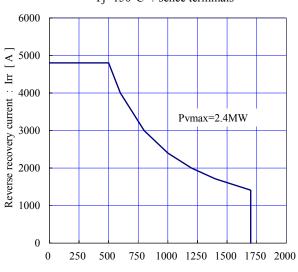
Switching loss vs. Gate resistance (typ.)



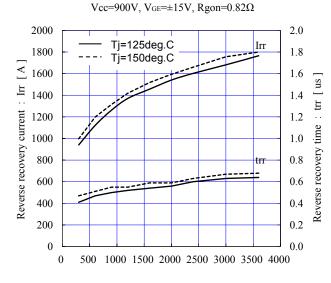




FWD safe operating area (max.) Tj=150°C / sence terminals



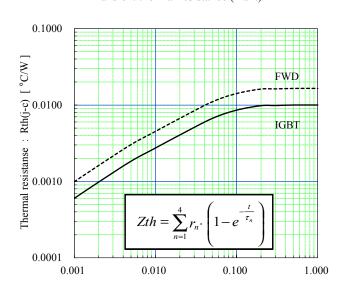
Collector-Emitter voltage: VCE [V]



Reverse recovery characteristics (typ.)

Forward current : IF [A]

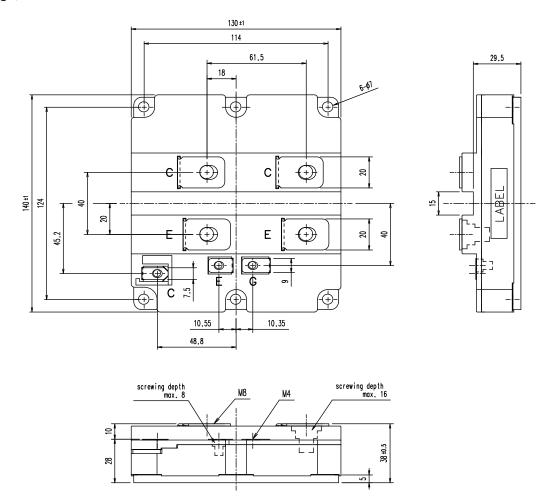
Transient thermal resistance (max.)



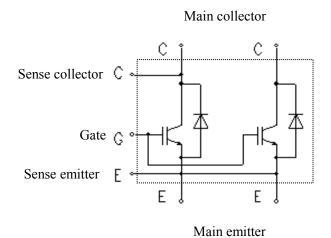
Pulse width: Pw [sec]

	IGBT	FWD
r1	0.00217	0.00275
r2	0.00317	0.00568
r3	0.00256	0.00447
r4	0.00210	0.00360
τ1	0.0078	0.0044
τ2	0.0473	0.0470
τ3	0.0596	0.0562
τ4	0.0783	0.0719

■ Outline Drawings, mm



■ Equivalent Circuit Schematic



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